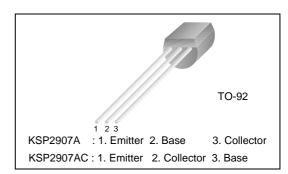


September 2006

KSP2907A PNP General Purpose Amplifier

Features

- Collector-Emitter Voltage: VcEo= 60V
- Collector Power Dissipation: Pc (max)=625mW
- Suffix "-C" means a Center Collector (1.Emitter 2.Collector 3.Base)
- Non suffix "-C" means a Side Collector (1.Emitter 2.Base 3.Collector)
- Available as PN2907A



Absolute Maximum Ratings * Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector current	-600	mA
T _J	Junction Temperature	+150	°C
T _{sta}	Storage Temperature	-55 ~ +150	°C

Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Max	Units
P _C	Collector Power Dissipation, by R _{0JA}	625	mW
$R_{\theta JC}$	Thermal Resistance, Junction to Case(note1)	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(note2)	200	°C/W

Note1. Infinite heat sink. Note2. Minimum Land pad size.

Electrical Characteristics * Ta = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = -10\mu A, I_E = 0$	-60			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = -10 \text{mA}, I_{B} = 0$	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-5.0			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = -50V, I_{E} = 0$			-10	nA
h_{FE}	DC Current Gain	$V_{CE} = -10V, I_{C} = -0.1mA,$	75			
		$V_{CE} = -10V, I_{C} = -1mA,$	100			
		$V_{CE} = -10V, I_{C} = -10mA,$	100			
		$V_{CE} = -10V, I_{C} = -150mA,$	100		300	
		$V_{CE} = -10V, I_{C} = -500mA,$	50			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$			-0.4	V
, ,		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$			-1.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{C} = -150 \text{mA}, I_{B} = -15 \text{mA}$			-1.3	V
, ,		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$			-2.6	V
C _{obo}	Output Capacitance	$V_{CB} = -10V, I_{E} = 0, f = 1.0MHz$			8	pF
f _T	Current Gain Bandwidth Product	I _C = -50mA, V _{CE} = -20V,	200			MHz
		f = 100MHz				
t _{ON}	Turn On Time	V_{CC} = -30V, I_{C} = -150mA, I_{B1} = -15mA			45	ns
t _{OFF}	Turn Off Time	V_{CC} = -6V, I_{C} = -150mA, I_{B1} = I_{B1} = -15mA			100	ns

^{*} DC Item are tested by Pulse Test: Pulse Width≤300us, Duty Cycle≤2%

^{*1.} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Package Marking and Ordering Information

Device(note)	Device Marking	Package	Packing Method	Qty(pcs)	Pin Definitions
KSP2907ABU	KSP2907A	TO-92	BULK		1.Emitter 2.Base 3.Collector
KSP2907ACBU	KSP2907AC	TO-92	BULK		1.Emitter 2.Collector 3.Base
KSP2907ATA	KSP2907A	TO-92	TAPE & AMMO	2,000	1.Emitter 2.Base 3.Collector
KSP2907ACTA	KSP2907AC	TO-92	TAPE & AMMO	2,000	1.Emitter 2.Collector 3.Base
KSP2907ATF	KSP2907A	TO-92	TAPE & REEL	2,000	1.Emitter 2.Base 3.Collector

Note: Affix "-C-" - center collector pin.
Suffix "-BU" - Bulk packing, straight lead form.(see package dimensions)
Suffix "-TF" - Tape& Reel packing, 0.200 In-Line Spacing lead form. (see package dimensions)
SUffix "-TA" - Tape& AMMO packing, 0.200 In-Line Spacing lead form. (see package dimensions)

Typical Characteristics

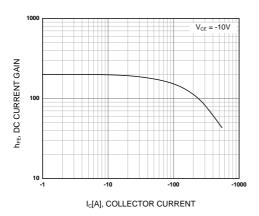


Figure 1. DC current Gain

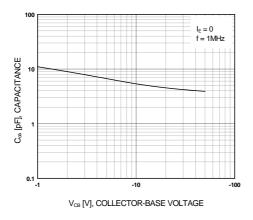


Figure 3. Output Capacitance

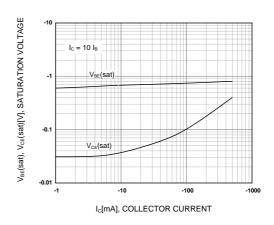


Figure 2. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

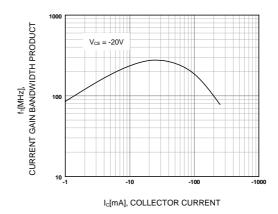
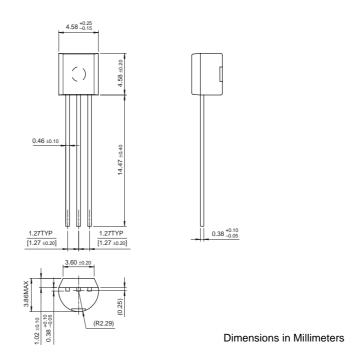


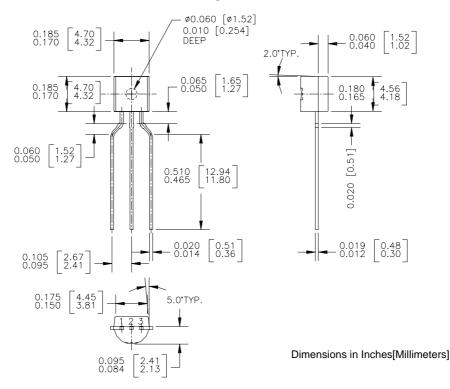
Figure 4. Current Gain Bandwidth Product

Package Dimensions

TO-92 Straight Lead Form



TO-92 0.200 In-Line Spacing Lead Form



UltraFET®

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PRODUCT STATUS DEFINITIONS

Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.		
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